

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1-8. (Canceled).

9. (Currently Amended) A micromechanical component for a sensor, comprising:

a body having a first substrate and a second substrate that form a hollow space; and  
a region of porous silicon located contiguously thereto, wherein the region of porous silicon is provided for lowering a pressure prevailing in the hollow space, in that a gas[[es]]  
[[are]] is bound to the porous silicon.

10. (Currently Amended) The component as recited in Claim 9, wherein the porous silicon binds oxygen by forming silicon dioxide ~~already~~ in response to a low temperature.

11. (Currently Amended) The component as recited in Claim 9, ~~further comprising:~~

~~a first substrate;~~  
~~a second substrate; and~~  
wherein an intermediate layer is provided between the first substrate and the second substrate, and wherein the porous silicon is in the second substrate.

12. (Previously Presented) The component as recited in Claim 11, wherein the first substrate and the second substrate are joined to one another in such a way that they are hermetically sealed at the intermediate layer.

13. (Currently Amended) The component as recited in Claim 9, further comprising:

~~a first substrate; and~~  
a membrane, wherein~~[[:]]~~ the hollow space is provided between the membrane and the first substrate, and the region of porous silicon is provided in the first substrate.

14. (Currently Amended) A method for manufacturing a sensor component, the method comprising:

producing a micromechanical structure in a first substrate;

producing in a second substrate a region of porous silicon;  
joining the first substrate and the second substrate; and  
lowering a pressure by activating the region of porous silicon.

15. (Currently Amended) A method for manufacturing a sensor component, the method comprising:

producing a region of porous silicon in a first substrate;  
producing in the first substrate a micromechanical structure; and  
joining a second substrate to the first substrate; and  
lowering a pressure by activating the region of porous silicon.

16. (Currently Amended) A method for manufacturing a sensor component, the method comprising:

producing a region of porous silicon in a first substrate;  
producing in the first substrate a micromechanical structure; and  
lowering a pressure by activating the region of porous silicon.

17-19. (Canceled).

20. (Currently Amended) The micromechanical component of Claim 9, ~~further comprising:~~  
wherein the micromechanical component is a micromechanical structure configured  
as a pressure sensor.

21. (Currently Amended) The method of Claim 14, wherein the micromechanical structure is ~~configured as a pressure sensor.~~

22. (New) A micromechanical pressure sensor, comprising:

a first substrate;  
a second substrate, wherein the first substrate is for bonding to the second substrate;  
and  
an intermediate layer provided between the first substrate and the second;  
a body having a hollow space and a region of porous silicon located contiguously  
thereto, wherein the region of porous silicon is arranged to lower a pressure prevailing in the  
hollow space by a gas being binded to the porous silicon.

23. (New) The sensor as recited in Claim 22, wherein the gas is oxygen, and the porous silicon binds the oxygen by forming silicon dioxide in response to a low temperature.

24. (New) The sensor as recited in Claim 22, wherein the first substrate and the second substrate are joined to one another so that they are hermetically sealed at the intermediate layer.

25. (New) The sensor as recited in Claim 22, wherein the hollow space is provided between the membrane and the first substrate, and the region of porous silicon is provided in the second substrate.

26. (New) The sensor as recited in Claim 22, wherein the hollow space is provided between the membrane and the first substrate, and the region of porous silicon is provided in the first substrate.

27. (New) The sensor as recited in Claim 22, wherein the porous silicon is used to provide a large surface area to provide effective getter characteristics.

28. (New) The sensor as recited in Claim 22, wherein the porous silicon is used to provide a large surface area of up to about  $1000 \text{ m}^2 \text{ per cm}^3$  to provide effective getter characteristics.

29. (New) The sensor as recited in Claim 22, wherein the porous silicon is used to eliminate the need for heating the component to high temperatures to activate getter characteristics of the porous silicon.

30. (New) The component as recited in Claim 9, wherein the porous silicon is used to provide a large surface area to provide effective getter characteristics.

31. (New) The component as recited in Claim 9, wherein the porous silicon is used to provide a large surface area of up to over  $1000 \text{ m}^2 \text{ per cm}^3$  to provide effective getter characteristics.

U.S. Patent Application No. 10/529,420

Attorney Docket No. 10191/3447

RCE Submission: Reply to Final Office Action of June 8, 2007

32. (New) The component as recited in Claim 9, wherein the porous silicon is used to eliminate the need for heating the component to high temperatures to activate getter characteristics of the porous silicon.